



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-60V	60mΩ@-10V	-4A
	66mΩ@-4.5V	

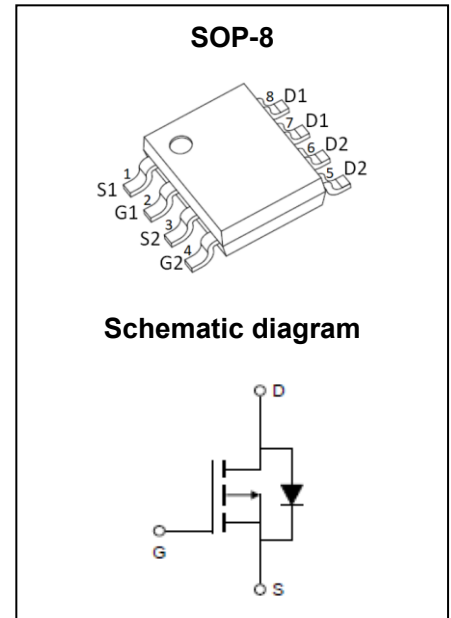
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge

Application

- Load Switch
- DC/DC Converter

MARKING:



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	-60	V
Gate - Source Voltage	V_{GS}	±20	V
Continuous Drain Current ^{1,5}	I_D	-4	A
Pulsed Drain Current ²	I_{DM}	-16	A
Single Pulsed Avalanche Current ⁴	I_{AS}	-18	A
Single Pulsed Avalanche Energy ⁴	E_{AS}	81	mJ
Power Dissipation ^{5,6}	P_D	3	W
Thermal Resistance from Junction to Ambient ⁶	$R_{\theta JA}$	41.7	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

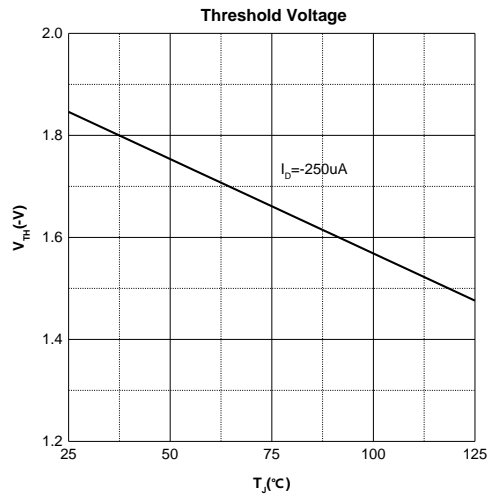
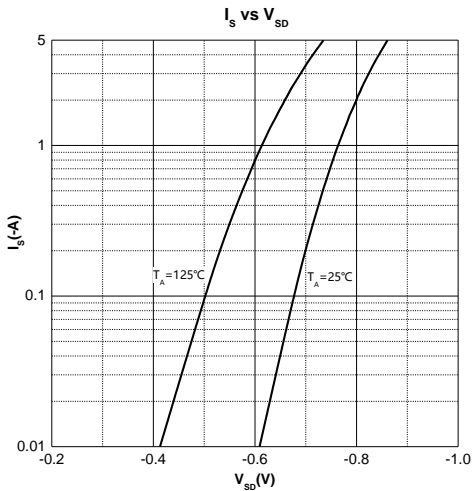
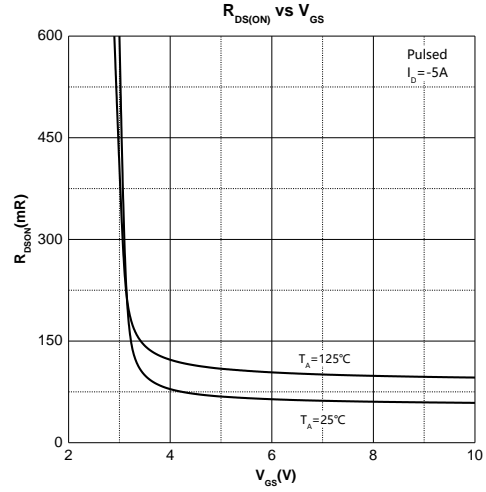
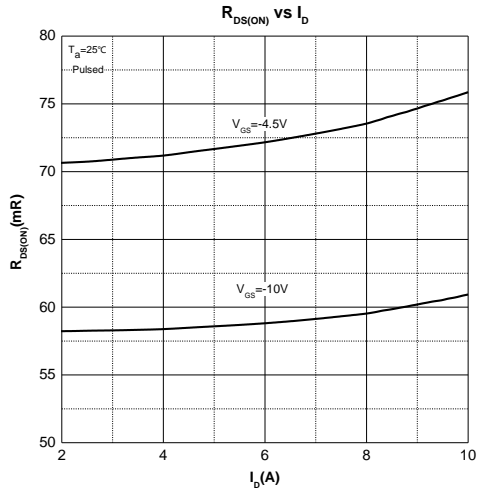
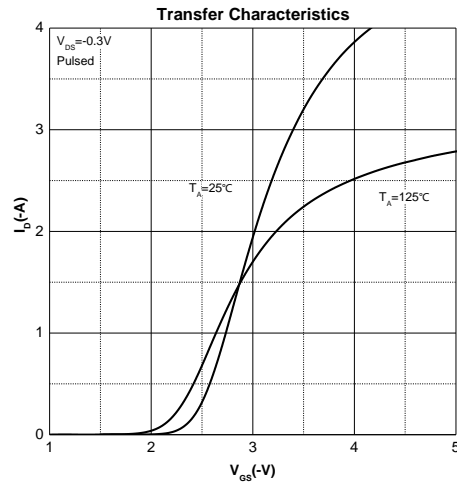
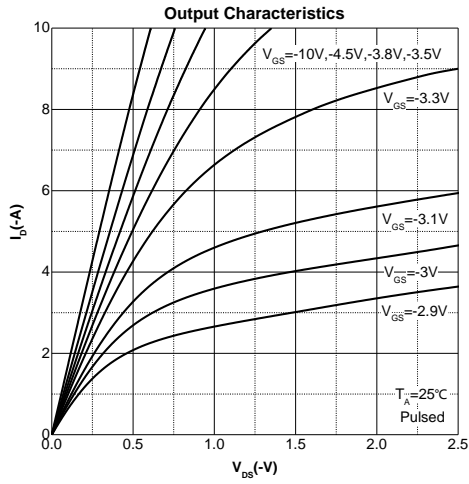
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics³						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-1.8	-3	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -5A$		60	78	m Ω
		$V_{GS} = -4.5V, I_D = -4A$		66	100	
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = -30V, V_{GS} = 0V, f = 1MHz$		1148		pF
Output Capacitance	C_{oss}			66		
Reverse Transfer Capacitance	C_{rss}			57		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		4.9		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = -30V, V_{GS} = -10V, I_D = -20A$		22		nC
Gate-source Charge	Q_{gs}			4.6		
Gate-drain Charge	Q_{gd}			3.6		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = -30V, V_{GS} = -10V,$ $R_L = 4.2\Omega, R_G = 3\Omega$		9		ns
Turn-on Rise Time	t_r			5		
Turn-off Delay Time	$t_{d(off)}$			31		
Turn-off Fall Time	t_f			7		
Source - Drain Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{GS} = 0V, I_S = -4A$			-1.2	V

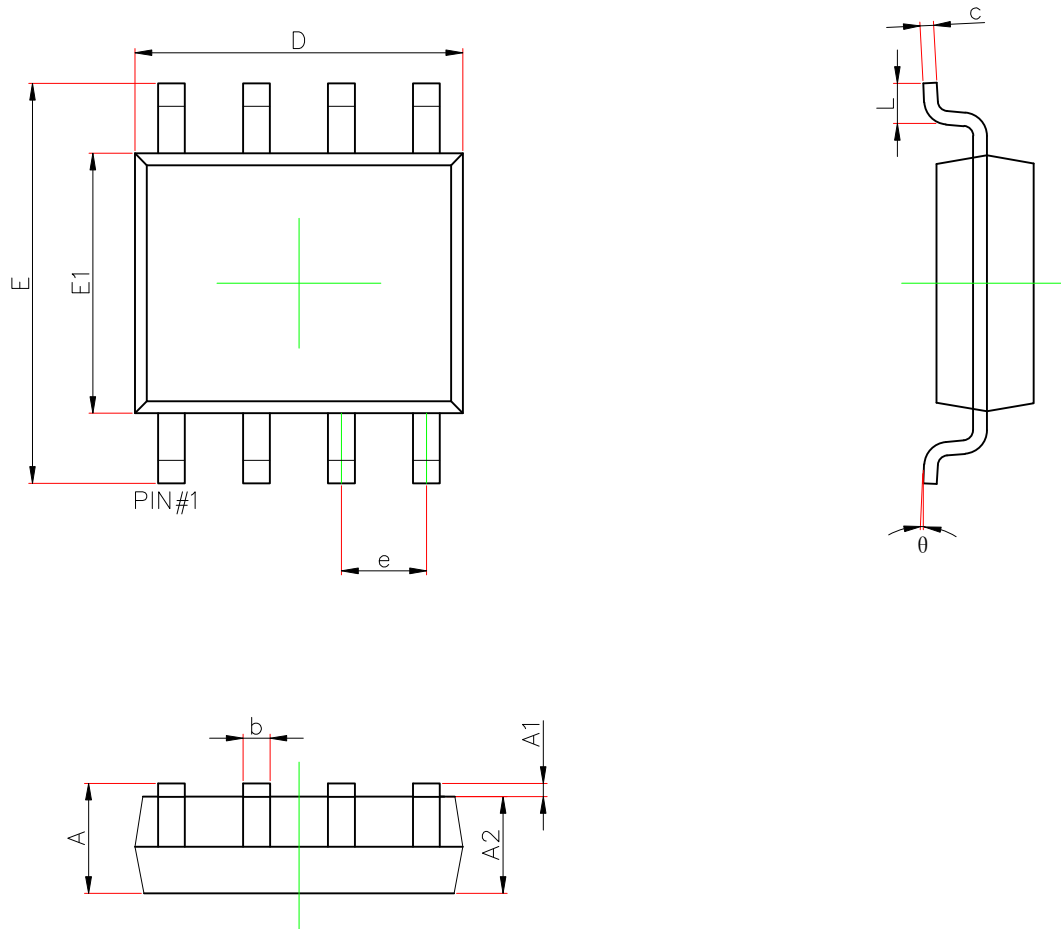
Notes :

- 1.The maximum current rating is limited by package.
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 4.EAS condition: $V_{DD} = -30V, V_{GS} = -10V, L = 0.5mH, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
- 5.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.
- 6.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics



SOP8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.156	0.250	0.006	0.010
D	4.700	5.100	0.185	0.201
e	1.270(BSC)		0.050(BSC)	
E	5.800	6.200	0.228	0.244
E1	3.700	4.100	0.146	0.161
L	0.400	1.270	0.016	0.05
θ	0°	8°	0°	8°